



IUMRS-ICEM 2018

AUGUST 19(SUN.) - 24(FRI.), 2018 / DAEJEON, KOREA

Session Title	Atomic Layer Deposition for Emerging Applications I	Session Code	Fr-C1
Date and Time	2018-08-24 / 8:30 - 10:30		
Place	Room C		
Session Chair	TBA		

Fr-C1-1

8:30 - 9:00

[Invited]Atomic Layer Deposition of 2D-WS₂ for High Performance Gas Sensor

Jusang Park
Yonsei Univ., Korea

Fr-C1-2

9:00 - 9:30

[Invited]Carbon/Oxide Coated/Wrapped Porous Silicon from Metallothermic Reactions for Lithium Ion Battery Applications

Zhihao Bao, Peibo Gao, and Xi Huang
Tongji Univ., China

Fr-C1-3

9:30 - 10:00

[Invited]Atomic Layer Deposition for Emerging Display Applications: From Functional Materials to Flexible Devices

Jin-Seong Park, Jiazhen Sheng, Seunghwan Lee, Taehyun Hong, Wanho Choi, and Gunho Ba
Hanyang Univ., Korea

Fr-C1-4

10:00 - 10:15

Damage-Reduced Bi-Layer Structure of Gate Dielectric for Improved MoS₂ FET Characteristics

Whang Je Woo, Il-Kwon Oh, Jeong-Gyu Song, Hanearl Jung, Bo-Eun Park, Jongseo Park, Kyunam Park, and
Hyungjun Kim
Yonsei Univ., Korea

Fr-C1-5

10:15 - 10:30

Improvement of Electrical Properties of ZrO₂ by Ta Incorporation for Emerging Higher-K Material

Bo-Eun Park, Il-Kwon Oh, Jong Seo Park, Seunggi Seo, and Hyungjun Kim
Yonsei Univ., Korea

Fr-C1-6

10:30 - 10:45

Effect of Oxidants on Atomic Layer Deposition of Al₂O₃: A DFT Study

Seunggi Seo¹, Taewook Nam¹, Han-Bo-Ram Lee², Hyungjun Kim¹, and Bonggeun Shong³
¹Yonsei Univ., Korea, ²Incheon Nat'l Univ., Korea, ³Hongik Univ., Korea